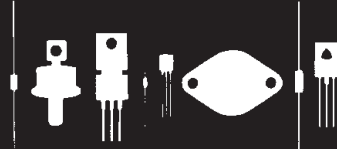


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145 Adams Avenue
Hauppauge, New York 11788



MPSA20 NPN
MPSA70 PNP

COMPLEMENTARY SILICON TRANSISTORS

JEDEC TO-92 CASE (EBC)

DESCRIPTION

The CENTRAL SEMICONDUCTOR MPSA20, MPSA70 types are complementary molded epoxy silicon transistors designed for general purpose amplifier and switching applications.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNIT
Collector-Emitter Voltage	V_{CE0}	40	V
Emitter-Base Voltage	V_{EBO}	4.0	V
Collector Current	I_C	100	mA
Power Dissipation	P_D	625	mW
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	1.5	W
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	.200	$^\circ\text{C}/\text{mW}$
Thermal Resistance	θ_{JC}	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CB0}	$V_{CB}=30\text{V}$		100	nA
BV_{CE0}	$I_C=1.0\text{mA}$	40		V
BV_{EBO}	$I_E=100\mu\text{A}$	4.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.25	V
h_{FE}	$V_{CE}=10\text{V}, I_C=5.0\text{mA}$	40	400	
f_T	$V_{CE}=10\text{V}, I_C=5.0\text{mA}, f=100\text{MHz}$	125		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=100\text{kHz}$		4.0	pF

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